

## **UNIVERSITI PUTRA MALAYSIA**

# PREPARATION AND CHARACTERIZATION OF BI2-O3-M2O5 (M = P,AS, V) OXIDE ION CONDUCTORS

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## PREPARATION AND CHARACTERIZATION OF $Bi_2O_3-M_2O_5$ (M = P, As, V) OXIDE ION CONDUCTORS

By

LEE SIEW LING

Thesis Submitted to the School of Graduate Studies, Universiti Putra Malaysia, in Fulfilment of the Requirements for the Degree of Doctor of Philosophy

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for Bon and family with love





Abstract of thesis presented to the Senate of Universiti Putra Malaysia in fulfilment of the requirement of the degree of Doctor of Philosophy

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#### May 2004

#### Chairman: Professor Lee Chnoong Kheng Ph.D.

#### **Faculty: Science and Environmental Studies**

 $Bi_2O_3-M_2O_5$ , M = P, As, V systems and related materials were prepared by solid state reactions. The phase purity of the materials was determined by X-ray diffraction (XRD). Further characterization using ac impedance spectroscopy and differential thermal analysis (DTA) were carried out on single phase materials. Besides, inductively coupled plasma-atomic emission spectrometry (ICP-AES), density measurement, thermogravimetric analysis (TGA), differential scanning calorimetry (DSC), scanning electron microscopy (SEM), Fourier-transform infrared (FT-IR) spectroscopy and Raman spectroscopy were also performed on selected materials. The crystal system and space group of the single phase materials were determined.

Two narrow solid solution series were formed in  $xBi_2O_3-P_2O_5$ : 5.5  $\leq x \leq 6$  and 7  $\leq x \leq$  7.25. In DTA study, a phase transition was clearly seen in  $Bi_7PO_{13}$  and  $Bi_{29}P_4O_{53.5}$  at ~860°C.



XRD shows that single phase materials were formed in  $xBi_2O_3-As_2O_5$  binary system when x = 5, 5.5, 5.667, 5.75, 6 and 7. Among these, materials in the composition range of  $5 \le x \le 6.25$  appeared to be solid solutions. Attempts to synthesize materials of composition of  $xBi_2O_3-As_2O_5$ ,  $1 \le x \le 4$  were unsuccessful.

Single phase materials were formed in  $xBi_2O_3-V_2O_5$  binary system,  $5 \le x \le 6$  and x = 7. A phase transition was observed in  $Bi_{17}V_3O_{33}$  and  $Bi_{23}V_4O_{44.5}$  at ~180°C. However, its origin is unknown.

Materials of composition  $xBi_2O_3-M_2O_5$ ,  $5.5 \le x \le 6$  (M = P) and  $5 \le x \le 6$  (M = As, V) are refined in triclinic symmetry with space group of *P-1*. Meanwhile, monoclinic symmetry was found in materials where x = 7, 7.25 (M = P) and x = 7(M = As, V). The XRD and IR patterns of both series of  $xBi_2O_3-As_2O_5$ ,  $5 \le x \le 6.25$  and  $xBi_2O_3-V_2O_5$ ,  $5.5 \le x \le 6$  solid solutions are very similar since these materials are isostructural. Generally, lattice parameters, volumes and densities of the materials in  $xBi_2O_3-M_2O_5$ system, M = P, As, V increased with the increase of Bi content.

A complete solid solution series was formed in the  $Bi_{22}P_4O_{43}$ - $Bi_{22}As_4O_{43}$ ,  $Bi_{22}P_4O_{43}$ - $Bi_{22}V_4O_{43}$ ,  $Bi_{22}As_4O_{43}$ - $Bi_{22}V_4O_{43}$ ,  $Bi_{23}P_4O_{44.5}$ - $Bi_{23}As_4O_{44.5}$ ,  $Bi_{23}P_4O_{44.5}$ - $Bi_{23}V_4O_{44.5}$ ,  $Bi_{23}As_4O_{44.5}$ - $Bi_{23}V_4O_{44.5}$ ,  $Bi_{12}P_2O_{23}$ - $Bi_{12}As_2O_{23}$ ,  $Bi_{12}P_2O_{23}$ - $Bi_{12}V_2O_{23}$ ,  $Bi_{12}As_2O_{23}$ - $Bi_{12}V_2O_{23}$ ,  $Bi_{12}As_2O_{13}$ - $Bi_{12}V_2O_{23}$ ,  $Bi_{12}As_2O_{23}$ - $Bi_{12}V_2O_{23}$ ,  $Bi_{12}As_2O_{13}$ - $Bi_{12}V_2O_{23}$ ,  $Bi_{12}As_2O_{13}$ - $Bi_{12}V_2O_{23}$ ,  $Bi_{12}As_2O_{13}$ - $Bi_{12}V_2O_{23}$ ,  $Bi_{12}As_2O_{13}$ - $Bi_{12}V_2O_{13}$ - $Bi_{12}V_2O_{13$ 



٧

content, followed by arsenic and phosphorus. Among the materials prepared, the highest conductivity is obtained in  $Bi_{23}V_4O_{44.5}$  with a  $\sigma$  value of 1.34 x 10<sup>-4</sup> ohm<sup>-1</sup> cm<sup>-1</sup> at 300°C. In an attempt to optimize oxide ion conductivity, chemical doping using PbO,  $Sr(NO_3)_2$ ,  $Al_2O_3$ ,  $Ga_2O_3$ ,  $La_2O_3$ ,  $Fe_2O_3$  *etc.* was carried out in selected materials, resulting in the formation of limited solid solutions. These materials, however, exhibit conductivity slightly lower than that of the parent materials.

Ball milling process has been carried out in the preparation of  $Bi_{23}V_4O_{44.5}$  and  $Bi_{14}PO_8$ in addition to manual grinding prior to firing of the samples. In ball milling process, high-density, fine-grained powders with uniform grain-size distribution were obtained, resulting in an increase in conductivity and dielectric constants.

Sillenite compounds in the Bi<sub>2</sub>O<sub>3</sub>-P<sub>2</sub>O<sub>5</sub> binary system with Bi:P ratios of 13:1 to 16:1 have been synthesized and found to be solid solutions. Substitution of P by V and As in the material where Bi:P = 14:1 results in partial and complete solid solutions, respectively. Enhancement in conductivity was observed in these solid solutions with V-doped materials exhibiting the highest conductivity. Substitution of P by elements such as Pb<sup>2+</sup>, Sr<sup>2+</sup>, Al<sup>3+</sup>, Ga<sup>3+</sup>, Fe<sup>3+</sup>, Si<sup>4+</sup>, Ge<sup>4+</sup>, and Ti<sup>4+</sup> leads to formation of limited solid solutions. Most of these materials have conductivity similar to or slightly higher than that of the parent compound. These materials appeared to be predominantly oxide ion conductors especially at temperatures above 800°C where  $\gamma \rightarrow \delta$ ' polymorphic transformation occurred.

## Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia sebagai memenuhi keperluan untuk ijazah Doktor Falsafah

#### PENYEDIAAN DAN PENCIRIAN KONDUKTUR ION OKSIDA Bi<sub>2</sub>O<sub>3</sub>-M<sub>2</sub>O<sub>5</sub> (M = P, As, V)

Oleh

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Sistem-sistem Bi<sub>2</sub>O<sub>3</sub>-M<sub>2</sub>O<sub>5</sub>, M = P, As, V dan bahan-bahan berkaitan telah disediakan melalui tindak balas keadaan pepejal. Ketulenan fasa bahan tersebut dikenalpastikan dengan penggunaan pembelauan sinar-X (XRD). Pencirian lanjutan telah dijalankan ke atas sampel yang berfasa tunggal dengan menggunakan spektroskopi impedans arus ulang-alik dan penganalisa pembezaan terma (DTA). Di samping itu, analisis-analisis termasuk analisis plasma induktif pasangan-pemancaran pengatoman (ICP-AES), penyukatan ketumpatan, analisis termogravimetri (TGA), kalorimetri pembezaan imbasan (DSC), mikroskopi imbasan elektron (SEM), spektroskopi infra merah transformasi Fourier (FT-IR) dan spektroskopi Raman telah dijalankan ke atas sampel-sampel terpilih. Sistem hablur dan kumpulan ruangan bagi sample-sampel yang berfasa tunggal juga dikenalpastikan.



Larutan pepejal telah terbentuk dalam sistem  $xBi_2O_3$ -P<sub>2</sub>O<sub>5</sub>: 5.5  $\leq x \leq 6$  dan 7  $\leq x \leq$  7.25. Dalam kajian DTA, suatu peralihan fasa didapati dalam Bi<sub>7</sub>PO<sub>13</sub> dan Bi<sub>29</sub>P<sub>4</sub>O<sub>53.5</sub> pada ~860°C.

XRD menunjukkan bahan berfasa tunggal telah terbentuk dalam sistem  $Bi_2O_3$ -As<sub>2</sub>O<sub>5</sub> apabila x = 5, 5.5, 5.667, 5.75, 6 and 7. Bahan-bahan dengan komposisi  $5 \le x \le 6.25$ wujud sebagai pepejal larutan. Percubaan untuk menyintesiskan komposisi  $xBi_2O_3$ -As<sub>2</sub>O<sub>5</sub>,  $1 \le x \le 4$  telah mengalami kegagalan.

Bahan berfasa tunggal terbentuk dalam sistem  $xBi_2O_3$ :  $V_2O_5$ ,  $5 \le x \le 6$  dan x = 7. Suatu peralihan fasa telah didapati dalam  $Bi_{17}V_3O_{33}$  dan  $Bi_{23}V_4O_{44.5}$  pada ~180°C. Tetapi, sifat asalnya tidak diketahui.

Sistem hablur bagi bahan-bahan berkomposisi  $xBi_2O_3-M_2O_5$ ,  $5.5 \le x \le 6$  (M = P) dan  $5 \le x \le 6$  (M = As, V) adalah bersimetri triklinik dengan kumpulan ruangan *P-1*. Sementara, sistem hablur bersimetri monoklinik didapati apabila x = 7, 7.25 (M = P) dan x = 7 (M = As, V). Pola XRD dan IR bagi kedua-dua siri pepejal larutan  $xBi_2O_3-As_2O_5$ ,  $5 \le x \le 6.25$  dan  $xBi_2O_3-V_2O_5$ ,  $5.5 \le x \le 6$  adalah mirip kerana mereka memiliki struktur yang serupa. Secara amnya, parameter kekisi, isipadu dan ketumpatan bahan-bahan dalam sistem  $xBi_2O_3-M_2O_5$ , M = P, As, V meningkat dengan penambahan kandungan Bi.



Siri larutan pepejal yang lengkap terbentuk dalam sistem-sistem  $Bi_{22}P_4O_{43}$ - $Bi_{22}As_4O_{43}$ ,  $Bi_{22}P_4O_{43}$ - $Bi_{22}V_4O_{43}$ ,  $Bi_{22}As_4O_{43}$ - $Bi_{22}V_4O_{43}$ ,  $Bi_{23}P_4O_{44.5}$ - $Bi_{23}As_4O_{44.5}$ ,  $Bi_{23}P_4O_{44.5}$ - $Bi_{23}As_4O_{44.5}$ ,  $Bi_{23}P_4O_{44.5}$ - $Bi_{23}As_4O_{44.5}$ ,  $Bi_{23}As_4O_{44.5}$ - $Bi_{23}As_4O_{44.5}$ ,  $Bi_{12}P_2O_{23}$ - $Bi_{12}As_2O_{23}$ ,  $Bi_{12}P_2O_{23}$ - $Bi_{12}V_2O_{23}$ ,  $Bi_{12}As_2O_{23}$ - $Bi_{12}V_2O_{23}$  dan  $Bi_7AsO_{13}$ - $Bi_7VO_{13}$ . Dalam sistem-sistem  $Bi_7PO_{13}$ - $Bi_7AsO_{13}$ dan  $Bi_7PO_{13}$ - $Bi_7VO_{13}$ , dua fasa yang berlainan telah dikesan. Bahan-bahan berfasa tunggal yang dikaji merupakan konduktor ion oksida. Kekonduksian meningkat dengan penambahan kandungan vanadium, diikuti oleh arsenik dan fosforus. Di antara bahanbahan yang disediakan,  $Bi_{23}V_4O_{44.5}$  telah menunjukkan kekonduksian yang paling tinggi dengan  $\sigma = 1.34 \times 10^{-4}$  ohm<sup>-1</sup> cm<sup>-1</sup> pada 300°C. Dalam usaha untuk meningkatkan kekonduksian, pendopan kimia dengan menggunakan PbO, Sr(NO\_3)\_2, Al\_2O\_3, Ga\_2O\_3, La\_2O\_3, Fe\_2O\_3 dan sebagainya telah dilakukan pada bahan-bahan terpilih. Pepejal larutan yang terhad telah terhasil. Walau bagaimanapun, kekonduksian bahan-bahan terdop tersebut adalah kurang daripada bahan-bahan induk.

Selain daripada tindak balas keadaan pepejal, proses pengisaran bebola juga dijalankan dalam penyediaan  $Bi_{23}V_4O_{44.5}$  dan  $Bi_{14}PO_{\delta}$ . Dalam proses pengisaran bebola, bahan yang berketumpatan tinggi, berserbuk halus dan bertaburan seragam telah dihasilkan, dan seterusnya membawa kepada peningkatan dalam kekonduksian dan pemalar dielektrik.

Kompoun sillenit dalam sistem  $Bi_2O_3$ - $P_2O_5$  dengan nisbah Bi:P berjulat antara 13:1 dan 16:1 telah disintesiskan dan larutan pepejal telah diperolehi dalam bahan-bahan tersebut. Penggantian P oleh V dalam  $Bi_{14}PO_{\delta}$  menghasilkan larutan pepejal yang

viii



terhad, sementara larutan pepejal yang lengap telah diperolehi apabila P dalam  $Bi_{14}PO_{\delta}$ digantikan oleh As. Peningkatan dalam kekonduksian telah diperhatikan dalam larutan pepejal yang didop dengan V. Pembentukan larutan pepejal yang terhad telah diperolehi apabila P digantikan oleh Pb<sup>2+</sup>, Sr<sup>2+</sup>, Al<sup>3+</sup>, Ga<sup>3+</sup>, Fe<sup>3+</sup>, Si<sup>4+</sup>, Ge<sup>4+</sup>, dan Ti<sup>4+</sup>. Kekonduksian bahan-bahan tersebut adalah lebih kurang sama dengan kompoun induk. Bahan-bahan tersebut merupakan konduktur ion oksida terutamanya pada suhu lebih daripada 800°C, di mana peralihan fasa  $\gamma \rightarrow \delta$ ' berlaku.



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xi



### TABLE OF CONTENTS

| DEDICATION                        | ii    |
|-----------------------------------|-------|
| ABSTRACT                          | iii   |
| ABSTRAK                           | vi    |
| ACKNOWLEDGEMENTS                  | Х     |
| APPROVAL                          | xii   |
| DECLARATION                       | xiv   |
| LIST OF TABLES                    | xix   |
| LIST OF FIGURES                   | xxiii |
| LIST OF ABBREVIATIONS AND SYMBOLS | xxxi  |
|                                   |       |

### CHAPTER

| 1 | INTRO | DUCTION  |      |
|---|-------|--|------|
|   | 1.1   | Solid Electrolytes and Oxide Ion Conductors        | 1.1  |
|   |       | 1.1.1 Ionic Conduction                             | 1.3  |
|   |       | 1.1.2 Solid Oxide Fuel Cell                        | 1.5  |
|   |       | 1.1.3 Oxygen Sensors                               | 1.8  |
|   | 1.2   | Solid Solutions                                    | 1.9  |
|   | 1.3   | Theory on Experimental Techniques                  | 1.10 |
|   |       | 1.3.1 X-ray Diffraction (XRD)                      | 1.10 |
|   |       | 1.3.2 Electrical Properties                        | 1.13 |
|   |       | 1.3.2.1 General Principles of the AC Method        | 1.14 |
|   |       | 1.3.2.2 Feasible Application of AC Impedance       |      |
|   |       | Spectroscopy                                       | 1.17 |
|   |       | 1.3.2.3 Cole-cole Plot                             | 1.18 |
|   |       | 1.3.2.4 Modulus Spectroscopy                       | 1.26 |
|   |       | 1.3.3 Thermal Analysis                             | 1.29 |
|   |       | 1.3.4 Scanning Electron Microscopy (SEM)           | 1.30 |
|   |       | 1.3.5 Fourier-transform Infrared (FT-IR) and Raman |      |
|   |       | Spectroscopy                                       | 1.30 |
|   |       | 1.3.6 X-ray Photoelectron Spectroscopy (XPS)       | 1.31 |
|   | 1.4   | Significance of Study                              | 1.32 |
|   | 1.5   | Objectives   | 1.33 |



| 2     | LITER | ATURE I                           | REVIEW   |      |
|-------|-------|-----------------------------------|--|------|
|       | 2.1   | Bi <sub>2</sub> O <sub>3</sub> (  | Oxide Ion Conductors   | 2.1  |
|       |       | 2.1.1                             | δ-Bi <sub>2</sub> O <sub>3</sub>   | 2.2  |
|       |       | 2.1.2                             | γ-Bi <sub>2</sub> O <sub>3</sub>   | 2.5  |
|       | 2.2   | Bi <sub>2</sub> O <sub>3</sub> -1 | P <sub>2</sub> O <sub>5</sub> Binary System                                  |      |
|       |       | 2.2.1                             | Polymorphism and Phase Diagram   | 2.8  |
|       |       | 2.2.2                             | Synthesis  | 2.12 |
|       |       | 2.2.3                             | Crystal Structures   | 2.17 |
|       |       | 2.2.4                             | Electrical Properties  | 2.25 |
|       |       | 2.2.5                             | Introduction of Dopant   | 2.26 |
|       | 2.3   | Bi <sub>2</sub> O <sub>3</sub> -  | As <sub>2</sub> O <sub>5</sub> Binary System                                 |      |
|       |       | 2.3.1                             | Synthesis  | 2.30 |
|       |       | 2.3.2                             | Crystal Structures   | 2.31 |
|       |       | 2.3.3                             | Polymorphism and Conductivity  | 2.35 |
|       | 2.4   | Bi2O3-                            | V <sub>2</sub> O <sub>5</sub> Binary System                                  |      |
|       |       | 2.4.1                             | Polymorphism and Phase Diagram   | 2.36 |
|       |       | 2.4.2                             | Synthesis  | 2.39 |
|       |       | 2.4.3                             | Crystal Structures   | 2.41 |
|       |       | 2.4.4                             | Electrical Properties  | 2.48 |
|       |       | 2.4.5                             | Introduction of Dopant   | 2.49 |
| 3 Exr | Expe  | rimental                          |  |      |
|       | 3.1   | Sample                            | e Preparation  |      |
|       |       | 3.1.1                             | Solid State Reaction with Manual Mixing                                      | 3.1  |
|       |       | 3.1.2                             | Solid State Reaction with Ball Milling Mixing                                | 3.2  |
|       |       | 3.1.3                             | Bi <sub>2</sub> O <sub>3</sub> -P <sub>2</sub> O <sub>5</sub> Binary System  | 3.3  |
|       |       | 3.1.4                             | Bi <sub>2</sub> O <sub>3</sub> -As <sub>2</sub> O <sub>5</sub> Binary System | 3.5  |
|       |       | 3.1.5                             | Bi <sub>2</sub> O <sub>3</sub> -V <sub>2</sub> O <sub>5</sub> Binary System  | 3.5  |

| 3.1.5 | Bi <sub>2</sub> O <sub>3</sub> -V <sub>2</sub> O <sub>5</sub> Binary System |  |
|-------|---|--|
|-------|---|--|

#### Pellet Preparation Characterization 3.2

## 3.3

|     | 0.1.0    |   |      |
|-----|----------|---|------|
| 3.2 | Pellet l | Preparation                                     | 3.6  |
| 3.3 | Charac   | terization                                      | 3.6  |
|     | 3.3.1    | X-ray Diffraction (XRD)                         | 3.7  |
|     | 3.3.2    | Electrical Properties                           | 3.8  |
|     | 3.3.3    | Thermal Analysis                                | 3.10 |
|     | 3.3.4    | Scanning Electron Microscopy (SEM)              | 3.12 |
|     | 3.3.5    | Fourier-transform Infrared (FT-IR) Spectroscopy | 3.12 |
|     | 3.3.6    | Raman Spectroscopy                              | 3.12 |
|     | 3.3.7    | Density Measurement                             | 3.13 |
|     | 3.3.8    | Inductively Coupled Plasma-Atomic Emission      |      |
|     |          | Spectrometry (ICP-AES)                          | 3.13 |
|     | 3.3.9    | Particle Size Analysis                          | 3.14 |
|     | 3.3.10   | X-ray Photoelectron Spectroscopy (XPS)          | 3.15 |
| 3.4 | Phase    | Diagram   | 3.15 |
|     | 3.4.1    | Melting Point                                   | 3.16 |
|     | 3.4.2    | Phase Stability                                 | 3.16 |
| 3.5 | Estima   | ation of Error                                  | 3.17 |
|     |          |   |      |

xvi

4 RESULTS AND DISCUSSION

| 4.1 | Bi <sub>2</sub> O <sub>3</sub> -P <sub>2</sub> O <sub>5</sub> Binary System   |        |
|-----|---|--------|
|     | 4.1.1 Phase Purity  | 4.1    |
|     | 4.1.2 Density Measurement   | 4.13   |
|     | 4.1.3 Element Determination   | 4.15   |
|     | 4.1.4 Electrical Properties   | 4.16   |
|     | 4.1.5 Thermal Analysis  | 4.30   |
|     | 4.1.6 Fourier-transform Infrared (FT-IR) and Raman  |        |
|     | Spectroscopy  | 4.32   |
| 4.2 | Bi <sub>2</sub> O <sub>3</sub> -As <sub>2</sub> O <sub>5</sub> Binary System  |        |
|     | 4.2.1 Phase Purity  | 4.39   |
|     | 4.2.2 Density Measurement   | 4.48   |
|     | 4.2.3 Element Determination   | 4.49   |
|     | 4.2.4 Electrical Properties   | 4.50   |
|     | 4.2.5 Thermal Analysis  | 4.57   |
|     | 4.2.6 Fourier-transform Infrared (FT-IR) and Raman  |        |
|     | Spectroscopy  | 4.60   |
| 4.3 | $Bi_2O_3 - V_2O_5$ Binary System  |        |
|     | 4.3.1 Phase Purity  | 4.65   |
|     | 4.3.2 Density Measurement   | 4.74   |
|     | 4.3.3 Element Determination   | 4.76   |
|     | 4.3.4 Electrical Properties   | 4.77   |
|     | 4.3.5 Thermal Analysis  | 4.97   |
|     | 4.3.6 Fourier-transform infrared (FI-IR)<br>$P_{i}^{i} = P_{i}^{i} =$ | 4.100  |
| 4.4 | $xB1_2O_3$ : (P/As/V) <sub>2</sub> O <sub>5</sub> Solid Solutions, $x = 5.5, 5.75, 6, 7$  | 4 100  |
|     | 4.4.1 Formation of Solid Solutions  | 4.102  |
|     | 4.4.2 Density Measurement   | 4.11/  |
|     | 4.4.5 Electrical Properties   | 4.120  |
|     | 4.4.4 Internal Analysis<br>4.4.5 Equation transform Infrared (ET ID)  | 4.123  |
|     | 4.4.5 Found-transform initiated (FI-IK)   | 4.155  |
|     | 4.4.0 Inflotucion of Dopants<br>4.4.6.1 Phase Purity  | 1 136  |
|     | 4.4.6.7 Flectrical Properties   | 4.130  |
| 45  | Sillenite and other Materials in Cubic Systems  | Ст1, г |
| 1.5 | 4.5.1 Phase Purity  | 4 148  |
|     | 4.5.2 Density Measurement   | 4 155  |
|     | 4.5.3 Elemental Determination   | 4.160  |
|     | 4.5.4 Electrical Properties   | 4.161  |
|     | 4.5.5 Thermal Analysis  | 4.182  |
|     | 4.5.6 Fourier-transform Infrared (FT-IR)  | 4.185  |
| 4.6 | $Bi_{14}P_{1-v}M_vO_{\delta}$ Solid Solutions   |        |
|     | 4.6.1 Formation of Solid Solutions  | 4.188  |
|     | 4.6.2 Density Measurement   | 4.202  |
|     | 4.6.3 Electrical Properties   | 4.204  |
|     | 4.6.4 Thermal Analysis  | 4.209  |
|     | 4.6.5 Fourier-transform Infrared (FT-IR)  | 4.214  |



| 5      | CONCLUSION  | 5.1 |
|--------|---|-----|
| REFE   | RENCES  | R.1 |
| APPE   | NDICES  | A.1 |
| BIOD   | ATA OF THE AUTHOR                                 | B.1 |
| LIST ( | OF PUBLICATIONS AND CONFERENCES/SEMINARS ATTENDED | C.1 |

xviii



### LIST OF TABLES

| Table |   | Page |
|-------|---|------|
| 1.1   | Equation for real axis intercepts in all four formalisms for three equivalent circuit in Figure 1.7                                 | 1.21 |
| 1.2   | Capacitance values and their possible interpretation (Sinclair et al., 2000)  | 1.23 |
| 2.1   | Conductivities of different phases of $Bi_2O_3$ measured between platinum electrodes  | 2.1  |
| 2.2   | List of elements doped in $\delta$ -Bi <sub>2</sub> O <sub>3</sub>  | 2.4  |
| 2.3   | Synthesis conditions of Bi-rich compounds in $Bi_2O_3$ - $P_2O_5$ binary system   | 2.13 |
| 2.4   | Structural data of compounds in $Bi_2O_3$ - $P_2O_5$ binary system, in the concentration range 50-85 mol% $P_2O_5$                  | 2.18 |
| 2.5   | Structural data of P-rich compounds in Bi2O3-P2O5 binary system   | 2.24 |
| 2.6   | Synthesis conditions of compounds in $Bi_2O_3$ - $V_2O_5$ binary system via solid solution reaction                                 | 2.40 |
| 2.7   | Structural data of compounds in $Bi_2O_3$ - $V_2O_5$ binary system  | 2.41 |
| 2.8   | Some characteristics of quenched films of $Bi_2O_3$ - $V_2O_5$ (Sekiya <i>et al.</i> , 1985)  | 2.47 |
| 2.9   | List of elements doped in Bi <sub>4</sub> V <sub>2</sub> O <sub>11</sub>  | 2.50 |
| 3.1   | Synthesis temperature of materials in xBi <sub>2</sub> O <sub>3</sub> -P <sub>2</sub> O <sub>5</sub> binary system                  | 3.4  |
| 3.2   | Wavelength of elements used and concentration of standard solutions prepared in ICP-AES analysis                                    | 3.14 |
| 3.3   | Estimation of error for experimental parameters   | 3.17 |
| 4.1   | The lattice parameters of $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> , $5.5 \le x \le 6$ solid solutions from X-ray diffraction data | 4.6  |
| 4.2   | Weight loss in sample where $Bi/P = 6.25$ and 6.5 in prolong heating treatment at $900^{\circ}C$                                    | 4.8  |



| 4.3  | The lattice parameters of $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> binary system, $x = 7$ and 7.25 from X-ray diffraction data   | 4.10 |
|------|---|------|
| 4.4  | Summary of $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> binary system, $5 \le x \le 9$   | 4.11 |
| 4.5  | Densities of $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> binary system, $5.5 \le x \le 7.25$  | 4.13 |
| 4.6  | Densities calculated from XRD results for $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> binary system, $5.5 \le x \le 6$  | 4.15 |
| 4.7  | Elemental composition of materials in $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> binary system, $5 \le x \le 7$  | 4.16 |
| 4.8  | Conductivity ( $\sigma_{300}$ and $\sigma_{600}$ ) and activation energy (E <sub>a</sub> ) of $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> binary system, $5.5 \le x \le 7.25$ | 4.22 |
| 4.9  | Raman band position of Bi23P4O44.5  | 4.36 |
| 4.10 | The lattice parameters of $xBi_2O_3$ -As $_2O_5$ binary system from X-ray diffraction data  | 4.45 |
| 4.11 | Densities of $xBi_2O_3$ -As <sub>2</sub> O <sub>5</sub> binary system, $5 \le x \le 7$  | 4.48 |
| 4.12 | Elemental composition of materials in $xBi_2O_3$ -As <sub>2</sub> O <sub>5</sub> binary system, $5 \le x \le 7$   | 4.49 |
| 4.13 | Conductivity ( $\sigma_{300}$ and $\sigma_{600}$ ) and activation energy (E <sub>a</sub> ) of $xBi_2O_3$ -As <sub>2</sub> O <sub>5</sub> , $5 \le x \le 7$                  | 4.53 |
| 4.14 | The lattice parameters of $xBi_2O_3-V_2O_5$ , $5 \le x \le 7$ solid solutions from X-ray diffraction data   | 4.71 |
| 4.15 | Densities of $xBi_2O_3$ -V <sub>2</sub> O <sub>5</sub> binary system, $5 \le x \le 7$   | 4.75 |
| 4.16 | Elemental composition of materials in $xBi_2O_3-V_2O_5$ binary system, $5 \le x \le 7$  | 4.76 |
| 4.17 | Particle size of $Bi_{23}V_4O_{44.5}$ prepared via solid state reaction with manual mixing and ball mill (bm) mixing  | 4.82 |
| 4.18 | Capacitance and the relative permittivity at $Z^{"}_{max}$ of $Bi_{23}V_4O_{44.5}$ taken in the 1 <sup>st</sup> cooling cycle   | 4.85 |
| 4.19 | Conductivity ( $\sigma_{300}$ and $\sigma_{600}$ ) and activation energy (E <sub>a</sub> ) of $xBi_2O_3-V_2O_5$ binary system, $5 \le x \le 7$                              | 4.91 |

.



| 4.20 | Lattice parameters of $5.5Bi_2O_3-M_2O_5$ , M = P, As, V solid solutions from X-ray diffraction data   | 4.113 |
|------|--|-------|
| 4.21 | Lattice parameters of $5.75Bi_2O_3-M_2O_5$ , M = P, As, V solid solutions from X-ray diffraction data  | 4.114 |
| 4.22 | Lattice parameters of $6Bi_2O_3-M_2O_5$ , M = P, As, V solid solutions from X-ray diffraction data   | 4.115 |
| 4.23 | Lattice parameters of $7Bi_2O_3$ -M <sub>2</sub> O <sub>5</sub> , M = P, As, V solid solutions from X-ray diffraction data   | 4.116 |
| 4.24 | Densities of Bi <sub>22</sub> P <sub>4-4x</sub> As <sub>4x</sub> O <sub>43</sub> solid solutions   | 4.118 |
| 4.25 | Densities of Bi <sub>22</sub> P <sub>4-4x</sub> V <sub>4x</sub> O <sub>43</sub> solid solutions  | 4.118 |
| 4.26 | Densities of $Bi_{22}As_{4-4x}V_{4x}O_{43}$ solid solutions  | 4.119 |
| 4.27 | Conductivity ( $\sigma_{300}$ and $\sigma_{600}$ ) and activation energy (E <sub>a</sub> ) of $xBi_2O_3-M_2O_5$ , M = P, As, V and related materials   | 4.124 |
| 4.28 | Phase purity of the doped materials in $5.75Bi_2O_3-M_2O_5$ , $M = P$ , As, V  | 4.138 |
| 4.29 | Conductivity ( $\sigma_{300}$ and $\sigma_{600}$ ) and activation energy (E <sub>a</sub> ) of 5.75Bi <sub>2</sub> O <sub>3</sub> -M <sub>2</sub> O <sub>5</sub> , M = P, V, As and related materials | 4.146 |
| 4.30 | Phases synthesized in $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> binary system, $10 \le x \le 25$   | 4.150 |
| 4.31 | The lattice parameters of sillenite materials from X-ray diffraction Data  | 4.154 |
| 4.32 | Densities of $Bi_x PO_{\delta}$ , $13 \le x \le 16$  | 4.157 |
| 4.33 | Densities calculated from XRD results for $Bi_x PO_{\delta}$ , $13 \le x \le 16$   | 4.159 |
| 4.34 | Elemental composition of materials $Bi_x PO_{\delta}$ , $13 \le x \le 16$  | 4.160 |
| 4.35 | Conductivity values of $Bi_{14}PO_{\delta}$ and related materials at 500°C and 800°C   | 4.168 |

xxi



| 4.36 | Particle size of $Bi_{14}PO_{\delta}$ prepared via solid state reaction with manual mixing and ball mill (bm) mixing          | 4.172 |
|------|---|-------|
| 4.37 | Capacitance and the relative permittivity at $Z^{"}_{max}$ of $Bi_{14}PO_{\delta}$ taken at the 1 <sup>st</sup> cooling cycle | 4.179 |
| 4.38 | DTA results of sillenite materials in Bi <sub>2</sub> O <sub>3</sub> -P <sub>2</sub> O <sub>5</sub> binary system             | 4.182 |
| 4.39 | Results of doping experiments on $Bi_{14}PO_{\delta}$ ( $Bi_{14}P_{1-x}M_{x}O_{\delta}$ )                                     | 4.188 |
| 4.40 | The lattice parameters of $Bi_{14}P_{1-x}As_xO_{\delta}$ from X-ray diffraction data  | 4.191 |
| 4.41 | Lattice parameters of $Bi_{14}P_{1-x}V_xO_\delta$ from X-ray diffraction data   | 4.196 |
| 4.42 | Densities of $Bi_{14}P_{1-x}As_xO_{\delta}$ solid solutions   | 4.203 |
| 4.43 | Densities of $Bi_{14}P_{1-x}V_xO_{\delta}$ , $0 \le x \le 0.3$ , solid solutions  | 4.203 |
| 4.44 | Conductivity values of Bi14AsO $_{\delta}$ and Bi14.3AsO $_{\delta}$ (6.52 mol% As <sub>2</sub> O <sub>5</sub> ) at 500°C     | 4.207 |
| 4.45 | Conductivity values of $Bi_{14}PO_{\delta}$ and doped materials at 500°C and 800°C  | 4.209 |
| 4.46 | DTA results of $Bi_{14}P_{1-x}V_xO_\delta$ solid solutions  | 4.213 |
| 4.47 | DTA results of $Bi_{14}P_{1-x}M_xO_\delta$ solid solutions  | 4.214 |



| Figures |   | Page |
|---------|---|------|
| 1.1     | Electrical conductivities of selected common substances and representative solid electrolytes (Greenblatt, 1994)  | 1.2  |
| 1.2     | Concept diagram of SOFC (Fisher, 1999)  | 1.7  |
| 1.3     | Principle of X-ray diffraction  | 1.12 |
| 1.4     | Admittance bridge   | 1.15 |
| 1.5     | Impedance bridge  | 1.15 |
| 1.6     | Semi-circle and spike in a complex Z* plot  | 1.19 |
| 1.7     | Possible equivalent circuits and its corresponding frequency response in complex plane plots for the four electrical formalisms (Hirose and West, 1996)   | 1.20 |
| 1.8     | Brickwork model of grain boundary regions in a ceramic placed between metal electrodes (Irvine et al., 1990)  | 1.22 |
| 1.9     | Equivalent circuit for a polycrystalline solid electrolyte:<br>$C_{dl}$ -electrode double-layer capacitance; $C_b$ , $R_b$ – bulk crystals;<br>$C_{gb}$ , $R_{gb}$ -grain boundaries  | 1.24 |
| 1.10    | Impedance diagram due to a blocking interface: (a) a perfectly smooth interface; (b) rough electrode or due to Warburg impedance (Armstrong and Todd, 1995)   | 1.25 |
| 1.11    | The Z" and M" spectroscopic plots respective to a complex Z* plot in Figure 1.7   | 1.29 |
| 2.1     | Structure models for $\delta$ -Bi <sub>2</sub> O <sub>3</sub> ; (a) Sillén model showing<br>ordered defects in <111> direction; (b) Gattow model:<br>average distribution of 6 oxygen atoms about the sites<br>of <i>Fm3m</i> | 2.3  |
| 2.2     | Outline of one unit cell of $Bi_{12}PbO_{19}$ in the sillenite phase showing the tetrahedra around each (2 <i>a</i> ) site cation and the O(2) and O(3) positions   | 2.8  |
| 2.3     | Equilibrium diagram of the Bi <sub>2</sub> O <sub>3</sub> -P <sub>2</sub> O <sub>5</sub> system (Volkov et al., 1983)   | 2.9  |

## LIST OF FIGURES



| 2.4  | Bi <sub>2</sub> O <sub>3</sub> -P <sub>2</sub> O <sub>5</sub> phase diagram in the concentration range 50-85 mol% $P_2O_5$ (Voevodskii <i>et al.</i> , 1997)  | 2.12 |
|------|---|------|
| 2.5  | Structure and cell relations of tetragonal $Bi_2O_2$ layers, with $O^{2-}$ in the layer plane and $Bi^{3+}$ above and below, respectively (Jie and Eysel, 1995)   | 2.22 |
| 2.6  | Distances in the coordination polyhedron of Bismuth. Standard deviation $\leq 0.010$ Å (Palkina and Jost, 1975)   | 2.25 |
| 2.7  | Planes of monoclinic lattice parameter of unlimited ternary solid solution in the system $Bi_{12}P_2O_{23}$ - $Bi_{12}As_2O_{23}$ - $Bi_{12}V_2O_{23}$ (Jie and Eysel, 1995)  | 2.29 |
| 2.8  | A view of the structure of $\alpha$ -BiAsO <sub>4</sub> (Bedlivy and Mereiter, 1982)  | 2.32 |
| 2.9  | Phase transition of $Bi_4V_2O_{11}$ (Abraham et al., 1988)  | 2.37 |
| 2.10 | $Bi_2O_3$ - $V_2O_5$ phase diagram over the composition range 0-15 mol% $V_2O_5$ (Kargin and Voevodskii, 1997)  | 2.38 |
| 3.1  | Flow chart for the synthesis process of samples   | 3.2  |
| 3.2  | Flow chart of methodology   | 3.7  |
| 4.1  | XRD patterns of $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> , $5 \le x \le 9$ :<br>(a) $x = 5$ , (b) $x = 5.25$ , (c) $x = 5.5$ , (d) $x = 5.75$ , (e) $x = 6$ , (f) $x = 6.25$ ,<br>(g) $x = 6.5$ , (h) $x = 6.75$ , (i) $x = 7$ , (j) $x = 7.25$ , (k) $x = 7.5$ , (l) $x = 8$ ,<br>(m) $x = 8.5$ , (n) $x = 9$ | 4.2  |
| 4.2  | Comparison of XRD pattern with ICDD using $\mu$ PDSM:<br>(a) 5Bi <sub>2</sub> O <sub>3</sub> -P <sub>2</sub> O <sub>5</sub> and (b) ICDD card number 26-220   | 4.3  |
| 4.3  | XRD pattern of Bi <sub>23</sub> P <sub>4</sub> O <sub>44.5</sub>  | 4.5  |
| 4.4  | XRD pattern of Bi <sub>7</sub> PO <sub>13</sub>   | 4.9  |
| 4.5  | Comparison of XRD pattern with ICDD using $\mu$ PDSM:<br>(a) 9Bi <sub>2</sub> O <sub>3</sub> -P <sub>2</sub> O <sub>5</sub> and (b) $\delta$ -Bi <sub>2</sub> O <sub>3</sub> (ICDD card number 27-52)   | 4.12 |
| 4.6  | Complex impedance plane plot for $Bi_{23}P_4O_{44.5}$ at (a) $300^{\circ}C$ , (b) $500^{\circ}C$  | 4.17 |
| 4.7  | A combined Z" and M" spectroscopic plots for $Bi_{23}P_4O_{44.5}$ at 300°C  | 4.20 |
| 4.8  | Arrhenius plots of $xBi_2O_3$ -P <sub>2</sub> O <sub>5</sub> binary system, $5.5 \le x \le 7.25$  | 4.21 |

xxiv

